

## ABSTRACT

Since a supporting wafer contains nitrogen of  $1 \times 10^{14}$  atoms/cm<sup>3</sup> and interstitial oxygen atom concentration,  $O_i$ , (old ASTM) of  $13 \times 10^{17}$  atoms/cm<sup>3</sup>, therefore a part of the metal impurities in an active layer wafer and the metal impurities in a bonded wafer can be captured by the BMD and the OSF in the wafer during the heat treatment after the bonding. Consequently, the contamination from the metal impurities in the active layer can be reduced.